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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known	
		Application Number	10/705,504
		Filing Date	November 10, 2003
		First Named Inventor	Leo Mathew et al.
		Group Art Unit	Unassigned - 2818
		Examiner Name	Unassigned
Sheet	1	of	1
		Attorney Docket Number	SC13161TP

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TH	B1	SINGER, Pete; "Dual Gate Control Provides Threshold Voltage Options"; Semiconductor International; November 1, 2003; 2pp: URL http://www.reed-electronics.com/semiconductor/index.asp?layout=article&articleId=CA331000&text=motorola&rid=0&rme=0&cfd=1	

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U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number -Kind Code ² (if known)			
THP	A-1	US - 6,583,469	06-24-2003	Fried et al.	
	A-2	US - 2003/113970 A1	06-19-2003	Fried et al.	
	A-3	US - 6,472,258	10-29-2002	Adkisson et al.	
	A-4	US - 6,458,662	10-01-2002	Yu	
	A-5	US - 6,433,609	08-13-2002	Voldman	
	A-6	US - 6,414,356	07-02-2002	Forbes et al.	
	A-7	US - 6,413,802	07-02-2002	Hu et al.	
	A-8	US - 6,396,108	05-28-2002	Krivokapic et al.	
	A-9	US - 6,372,559	04-16-2002	Crowder et al.	
	A-10	US - 6,355,961	03-12-2002	Forbes	
	A-11	US - 6,330,184	12-11-2001	White et al.	
	A-12	US - 6,300,182	10-09-2001	Yu	
	A-13	US - 6,097,065	08-01-2000	Forbes et al.	
	A-14	US - 6,150,687	11-21-2000	Noble et al.	
	A-15	US - 6,011,725	01-04-2000	Eitan	
	A-16	US - 5,804,848	09-08-1998	Mukai	
	A-17	US - 5,689,127	11-18-1997	Chu et al.	
THP	A-18	US -4,859,623	08-22-1989	Busta	
		US -			
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ²	Number ⁴ Kind Code ³ (if known)			
TH	A-19	DE	101 25 967 C1	05-29-2001	Schlösser et al.	
TH	A-20	WO	00/21118	04-13-2000	Marso et al.	

NON PATENT LITERATURE DOCUMENTS		
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
TH	A-21	Related Application 10/074,732 entitled "Method of Forming a Vertical Double Gate Semiconductor Device and Structure Thereof" filed September 3, 2002 entitled
	A-22	Related Application 10/443,375 entitled "Transistor With Independent Gate Structures" filed May 22, 2003
	A-23	Related Application 10/443,908 "Memory with Charge Storage Locations" entitled filed May 22, 2003
TH	A-24	Related Application 10/427,141 entitled "Semiconductor Fabrication Process with Asymmetrical Conductive Spacers" filed April 30, 2003
TH	A-25	LEE et al.; "Multilevel Vertical-Channel SONOS Nonvolatile Memory on SOI"; IEEE Electron Device Letters, 2002; pp 1-3 and 208-209.
TH	A-26	YU, BIN et al; "FinFET Scaling to 10nm Gate Length"; IEEE IDEM 2002; pp 251-254; IEEE

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NON PATENT LITERATURE DOCUMENTS (CONT.)			
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PH	A-27	CHOI, YANG-KYU et al.; "Sub-20nm CMOS FinFET Technologies"; 2001 IEEE, 4 pp..	
	A-28	KEDZIERSKI, JAKUB et al.; "High-Performance Symmetric-Gate and CMOS-Compatible VI Asymmetric-Gate FinFET Devices"; 2001; IEEE; 4 pp.	
	A-28	HISAMOTO, DIGH et al.; "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20 nm"; IEEE Transactions on Electron Devices; Vol. 47, No. 12, December 2000, pp 2320-2325.	
	A-30	TANAKA, TETSU et al.; "Ultrafast Operation of V _{th} -Adjusted ^{PMOS} Double Gate SOI MOSFET's; IEEE Electron Device Letters, Vol 15, No. 10, October 1994; pgs 386-388.	
	A-31	CHAN et al.; "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device"; IEEE Electron Device Letters; March 1987; pp 93-95; Vol. EDL-8, No. 3.	
	A-32	GONZALEZ, FERNANDO Sr. et al.; "A Dynamic Source-Drain Extension (DSDE) MOSFET Using a Separately Biased Conductive Spacer"; pp 645-648	
	A-33	KIM, KEUNWOO et al.; "Double-Gate CMOS Symmetrical - Versus Asymmetrical-Gate Devices"; IEEE Transactions On Electron Devices, Vol 48, No. 2; February 2001; pp 294-299.	
PH	A-34	FOSSUM, JERRY G. et al.; "Extraordinarily High Drive currents in Asymmetrical Double-Gate MOSFETs"; Superlattices and Microstructures, Vol 28, No. 5/6, 2000, 2000 Academic Press, pp 525-530.	

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